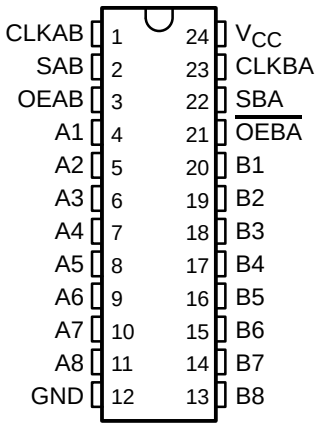
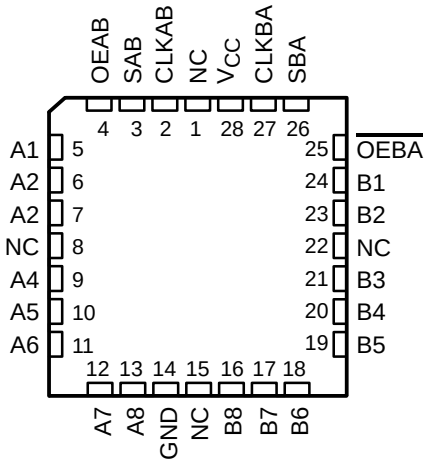
- **State-of-the-Art *EPIC*-II*B*™ BiCMOS Design Significantly Reduces Power Dissipation**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17**
- **Typical V_{OLP} (Output Ground Bounce) < 1 V at V_{CC} = 5 V, T_A = 25°C**
- **High-Drive Outputs (–32-mA I_{OH}, 64-mA I_{OL})**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Package, and Plastic (NT) and Ceramic (JT) DIPs**

SN54ABT652A . . . JT OR W PACKAGE
SN74ABT652A . . . DB, DW, NT, OR PW PACKAGE
(TOP VIEW)



SN54ABT652A . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These devices consist of bus-transceiver circuits, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the data bus or from the internal storage registers.

Output-enable (OEAB and $\overline{\text{OEBA}}$) inputs are provided to control the transceiver functions. Select-control (SAB and SBA) inputs are provided to select either real-time or stored data for transfer. The circuitry used for select control eliminates the typical decoding glitch that occurs in a multiplexer during the transition between stored and real-time data. A low input selects real-time data, and a high input selects stored data. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the ’ABT652A.

Data on the A- or B-data bus, or both, can be stored in the internal D-type flip-flops by low-to-high transitions at the appropriate clock (CLKAB or CLKBA) inputs, regardless of the select- or enable-control inputs. When SAB and SBA are in the real-time transfer mode, it is possible to store data without using the internal D-type flip-flops by simultaneously enabling OEAB and $\overline{\text{OEBA}}$. In this configuration, each output reinforces its input. When all other data sources to the two sets of bus lines are at high impedance, each set of bus lines remains at its last state.

To ensure the high-impedance state during power up or power down, $\overline{\text{OEBA}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver (B to A). OEAB should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver (A to B).

description (continued)

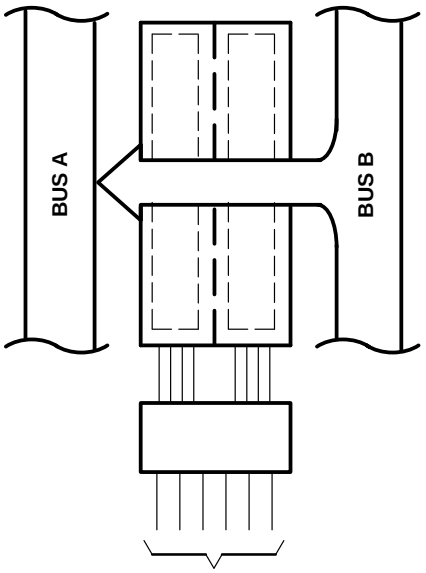
The SN54ABT652A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74ABT652A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS						DATA I/O†		OPERATION OR FUNCTION
OEAB	$\overline{\text{OEBA}}$	CLKAB	CLKBA	SAB	SBA	A1–A8	B1–B8	
L	H	H or L	H or L	X	X	Input	Input	Isolation
L	H	↑	↑	X	X	Input	Input	Store A and B data
X	H	↑	H or L	X	X	Input	Unspecified‡	Store A, hold B
H	H	↑	↑	X‡	X	Input	Output	Store A in both registers
L	X	H or L	↑	X	X	Unspecified‡	Input	Hold A, store B
L	L	↑	↑	X	X‡	Output	Input	Store B in both registers
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
H	H	X	X	L	X	Input	Output	Real-time A data to B bus
H	H	H or L	X	H	X	Input	Output	Stored A data to B bus
H	L	H or L	H or L	H	H	Output	Output	Stored A data to B bus and stored B data to A bus

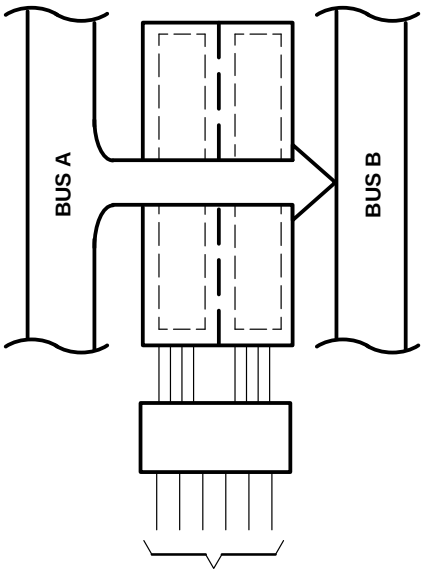
† The data-output functions may be enabled or disabled by a variety of level combinations at OEAB or $\overline{\text{OEBA}}$. Data-input functions are always enabled; i.e., data at the bus terminals is stored on every low-to-high transition of the clock inputs.

‡ Select control = L; clocks can occur simultaneously.
Select control = H; clocks must be staggered to load both registers.



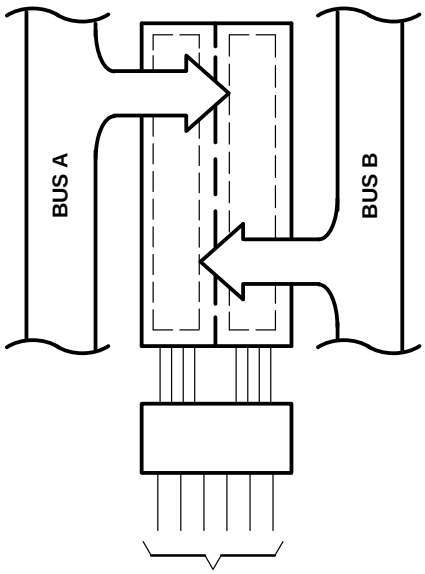
3	21	1	23	2	22
OEAB	$\overline{\text{OEBA}}$	CLKAB	CLKBA	SAB	SBA
L	L	X	X	X	L

REAL-TIME TRANSFER
BUS B TO BUS A



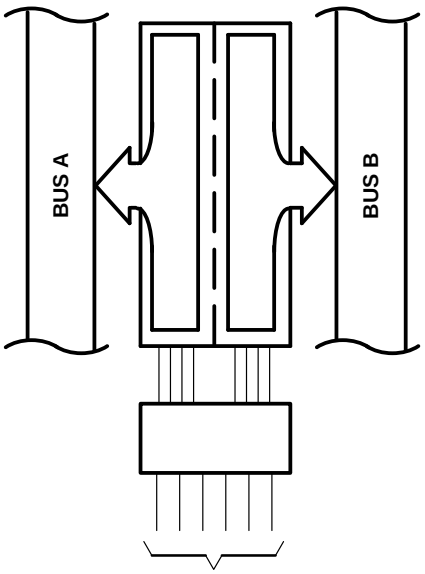
3	21	1	23	2	22
OEAB	$\overline{\text{OEBA}}$	CLKAB	CLKBA	SAB	SBA
H	H	X	X	L	X

REAL-TIME TRANSFER
BUS A TO BUS B



3	21	1	23	2	22
OEAB	$\overline{\text{OEBA}}$	CLKAB	CLKBA	SAB	SBA
X	H	↑	X	X	X
L	X	X	↑	X	X
L	H	↑	↑	X	X

STORAGE FROM
A, B, OR A AND B



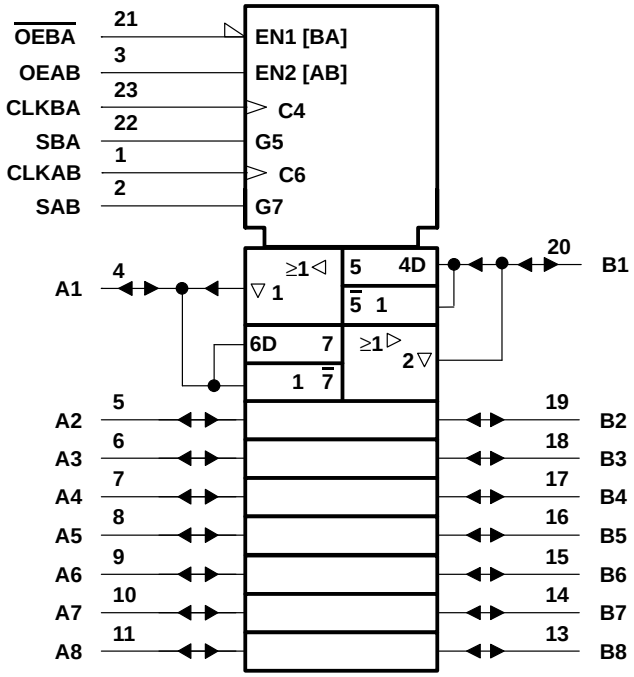
3	21	1	23	2	22
OEAB	$\overline{\text{OEBA}}$	CLKAB	CLKBA	SAB	SBA
H	L	H or L	H or L	H	H

TRANSFER STORED DATA
TO A AND/OR B

Pin numbers shown are for the DB, DW, JT, NT, PW, and W packages.

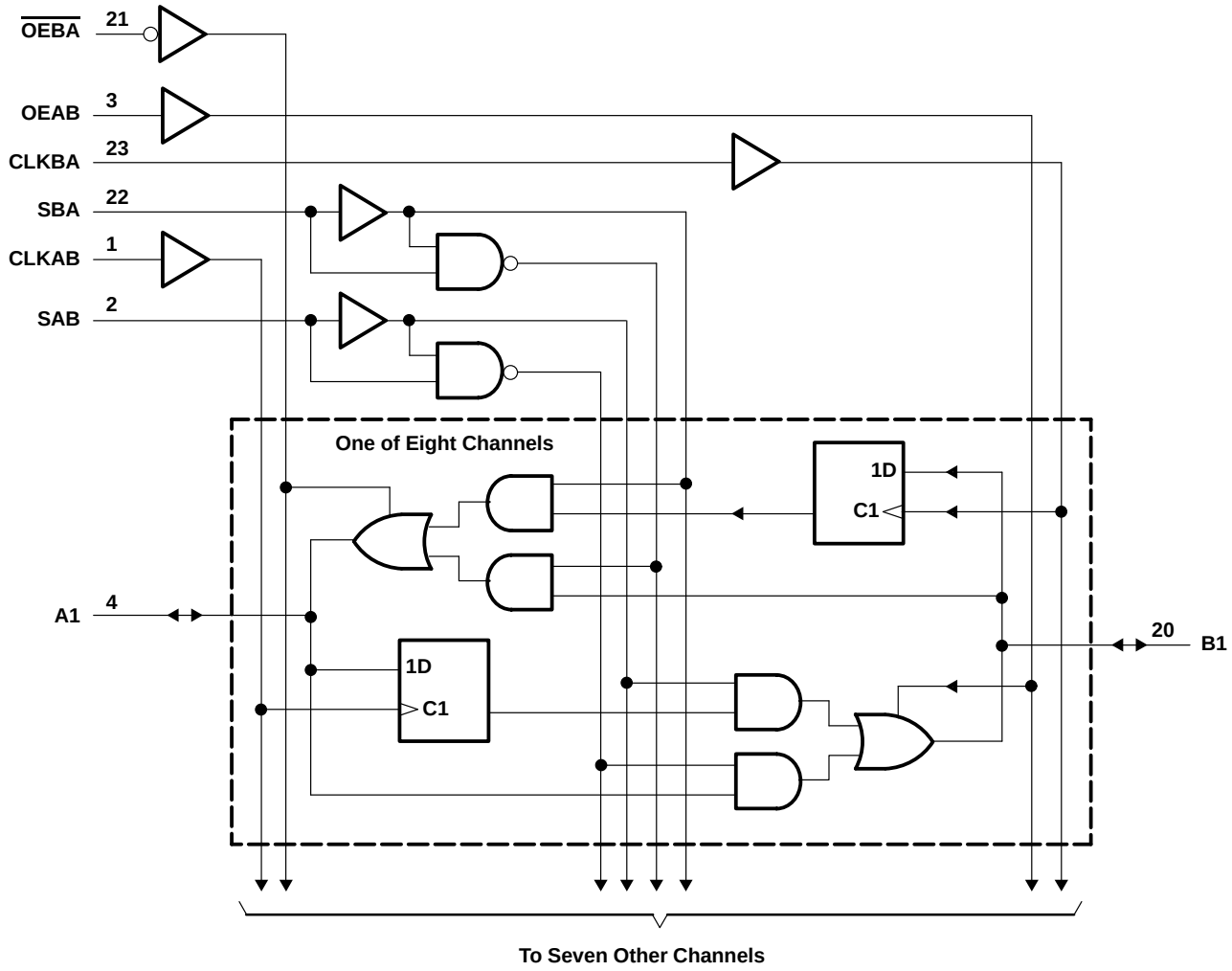
Figure 1. Bus-Management Functions

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the DB, DW, JT, NT, PW, and W packages.

logic diagram (positive logic)



Pin numbers shown are for the DB, DW, JT, NT, PW, and W packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 7 V
Input voltage range, V_I (except I/O ports) (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O . . . . . –0.5 V to 5.5 V
Current into any output in the low state, I_O: SN54ABT652A . . . . . 96 mA
SN74ABT652A . . . . . 128 mA
Input clamp current, I_{IK} (V_I < 0) . . . . . –18 mA
Output clamp current, I_{OK} (V_O < 0) . . . . . –50 mA
Package thermal impedance, θ_{JA} (see Note 2): DB package . . . . . 104°C/W
DW package . . . . . 81°C/W
NT package . . . . . 67°C/W
PW package . . . . . 120°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51, except for through-hole packages, which use a trace length of zero.

recommended operating conditions (see Note 3)

			SN54ABT652A		SN74ABT652A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		4.5	5.5	4.5	5.5	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		5		5	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 3: Unused pins (input or I/O) must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T_A = 25°C			SN54ABT652A		SN74ABT652A		UNIT
				MIN	TYP†	MAX	MIN	MAX	MIN	MAX	
V_{IK}		V_{CC} = 4.5 V,	I_I = –18 mA			–1.2		–1.2		–1.2	V
V_{OH}		V_{CC} = 4.5 V,	I_{OH} = –3 mA	2.5			2.5		2.5		V
		V_{CC} = 5 V,	I_{OH} = –3 mA	3			3		3		
		V_{CC} = 4.5 V	I_{OH} = –24 mA	2			2				
			I_{OH} = –32 mA	2*					2		
V_{OL}		V_{CC} = 4.5 V	I_{OL} = 48 mA			0.55		0.55			V
			I_{OL} = 64 mA			0.55*				0.55	
V_{hys}					100						mV
I_I	Control inputs	V_{CC} = 5.5 V,	V_I = V_{CC} or GND			±1		±1		±1	µA
	A or B ports					±100		±100		±100	
I_{OZH}‡		V_{CC} = 5.5 V,	V_O = 2.7 V			50**		10		50	µA
I_{OZL}‡		V_{CC} = 5.5 V,	V_O = 0.5 V			–50**		–10		–50	µA
I_{off}		V_{CC} = 0,	V_I or V_O ≤ 4.5 V			±100				±100	µA
I_{CEX}		V_{CC} = 5.5 V, V_O = 5.5 V	Outputs high			50		50		50	µA
I_O§		V_{CC} = 5.5 V,	V_O = 2.5 V	–50	–100	–180	–50	–180	–50	–180	mA
I_{CC}		V_{CC} = 5.5 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			250		250		250	µA
			Outputs low			30		30		30	mA
			Outputs disabled			250		250		250	µA
ΔI_{CC}¶		V_{CC} = 5.5 V, One input at 3.4 V, Other inputs at V_{CC} or GND				1.5		1.5		1.5	mA
C_i	Control inputs	V_I = 2.5 V or 0.5 V			7						pF
C_{io}	A or B ports	V_O = 2.5 V or 0.5 V			12						pF

* On products compliant to MIL-PRF-38535, this parameter does not apply.
** These limits apply only to the SN74ABT652A.
† All typical values are at V_{CC} = 5 V.
‡ The parameters I_{OZH} and I_{OZL} include the input leakage current.
§ Not more than one output should be tested at a time, and the duration of the test should not exceed one second.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 2)

		SN54ABT652A				UNIT
		V_{CC} = 5 V, T_A = 25°C		MIN	MAX	
		MIN	MAX			
f_{clock}	Clock frequency	0	125	0	125	MHz
t_w	Pulse duration, CLK high or low	4		4		ns
t_{su}	Setup time, A or B before CLKAB↑ or CLKBA↑	3		3.5		ns
t_h	Hold time, A or B after CLKAB↑ or CLKBA↑	1.5		1.5		ns

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 2)

		SN74ABT652A				UNIT
		V_{CC} = 5 V, T_A = 25°C		MIN	MAX	
		MIN	MAX			
f_{clock}	Clock frequency	0	125	0	125	MHz
t_w	Pulse duration, CLK high or low	4		4		ns
t_{su}	Setup time, A or B before CLKAB↑ or CLKBA↑	3		3		ns
t_h	Hold time, A or B after CLKAB↑ or CLKBA↑	0		0		ns

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54ABT652A					UNIT
			V_{CC} = 5 V, T_A = 25°C			MIN	MAX	
			MIN	TYP	MAX			
f_{max}			125	200		125		MHz
t_{PLH}	CLK	B or A	2.2	4	5.1	1.7	5.9	ns
t_{PHL}			1.7	4	5.1	1.7	5.9	
t_{PLH}	A or B	B or A	1.5	3	4.8	1	5	ns
t_{PHL}			1.5	3.3	4.6	1	5.6	
t_{PLH}	SAB or SBA†	B or A	1.5	4	5.5	1.5	6.8	ns
t_{PHL}			1.5	3.6	4.9	1.5	6.2	
t_{PZH}	$\overline{OEBA}$	A	2	3.6	5.4	2	6.8	ns
t_{PZL}			3	5.7	7.7	3	9.2	
t_{PHZ}	$\overline{OEBA}$	A	1.5	3.2	5.8	1	7.5	ns
t_{PLZ}			1.5	3	4.3	1	4.6	
t_{PZH}	OEAB	B	2	4.3	6.1	2	7.8	ns
t_{PZL}			3	5.5	7.4	3	8.9	
t_{PHZ}	OEAB	B	1.5	3.3	6	1	8	ns
t_{PLZ}			1.5	3.4	5	1.5	6.8	

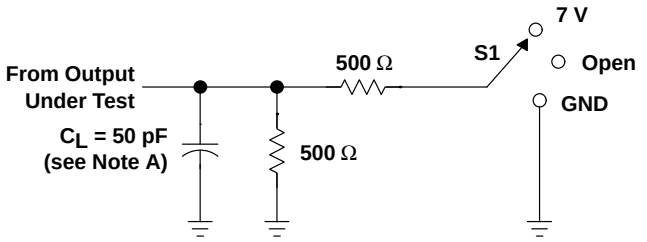
† These parameters are measured with the internal output state of the storage register opposite that of the bus input.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN74ABT652A					UNIT
			V_{CC} = 5 V, T_A = 25°C			MIN	MAX	
			MIN	TYP	MAX			
f_{max}			125	200		125		MHz
t_{PLH}	CLK	B or A	2.2	4	5.1	2.2	5.6	ns
t_{PHL}			1.7	4	5.1	1.7	5.6	
t_{PLH}	A or B	B or A	1.5	3	4.3	1.5	4.8	ns
t_{PHL}			1.5	3.3	4.6	1.5	5.4	
t_{PLH}	SAB or SBA†	B or A	1.5	4	5.1	1.5	6.5	ns
t_{PHL}			1.5	3.6	4.9	1.5	5.9	
t_{PZH}	$\overline{OEBA}$	A	2	3.6	4.6	2	5.8	ns
t_{PZL}			3	5.7	6.8	3	8.5	
t_{PHZ}	$\overline{OEBA}$	A	1.5	3.2	4.5	1.5	5	ns
t_{PLZ}			1.5	3	3.8	1.5	4.1	
t_{PZH}	OEAB	B	2	4.3	6.1	2	6.5	ns
t_{PZL}			3	5.5	6.5	3	7.4	
t_{PHZ}	OEAB	B	1.5	3.3	4.5	1.5	5.5	ns
t_{PLZ}			1.5	3.4	4.4	1.5	5.1	

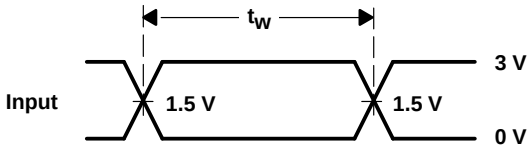
† These parameters are measured with the internal output state of the storage register opposite that of the bus input.

PARAMETER MEASUREMENT INFORMATION

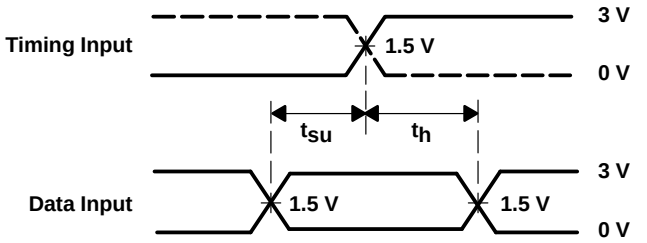


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	7 V
t_{PHZ}/t_{PZH}	Open

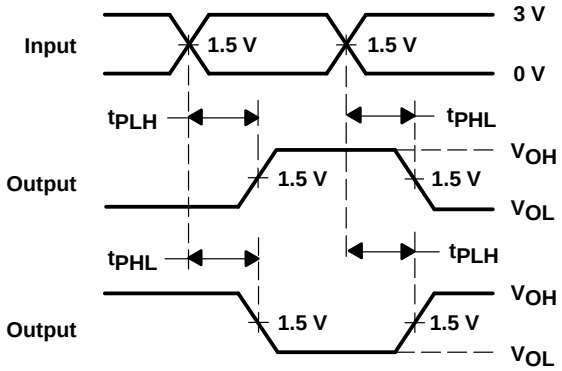
LOAD CIRCUIT



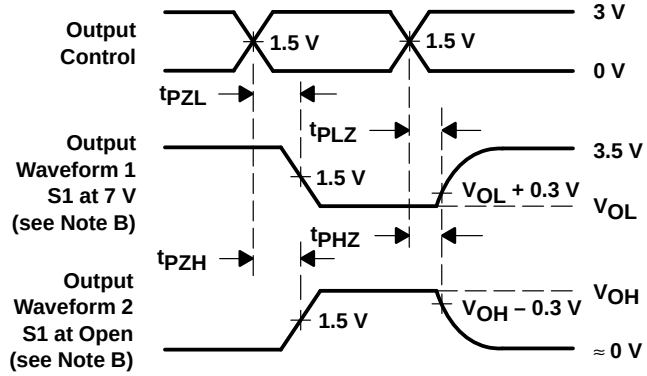
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 2. Load Circuit and Voltage Waveforms

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